

CI  
Concl 10

a gate electrode formed above the silicon substrate between the pair of impurity diffused regions with a gate insulation film interposed therebetween, the gate electrode being formed of a first polycrystalline silicon film formed on the gate insulation film, a second polycrystalline silicon film formed on the first polycrystalline silicon film having a thickness of 2-20 nm and thinner than that of the first polycrystalline silicon film and having crystal grain boundaries which are discontinuous to the first polycrystalline silicon film, and a metal nitride film formed on the second polycrystalline silicon film.

2. (Twice Amended) A semiconductor device comprising:

a pair of impurity diffused regions formed in a silicon substrate, spaced from each other; and  
a gate electrode formed above the silicon substrate between the pair of impurity diffused regions with a gate insulation film interposed therebetween, the gate electrode being formed of a first polycrystalline silicon film formed on the gate insulation film, a second polycrystalline silicon film formed on the first polycrystalline silicon film having a thickness of 2-20 nm and thinner than that of the first polycrystalline silicon film and having crystal grain boundaries which are discontinuous to the first polycrystalline silicon film, a metal nitride film formed on the second polycrystalline silicon film, and a metal film form on the metal nitride film.

---

CA

3. (Amended) A semiconductor device according to claim 1, wherein

a native oxide film or a chemical oxide film formed by liquid chemical treatment is formed between the first polycrystalline silicon film and the second polycrystalline silicon film.

CA  
concl.

4. (Amended) A semiconductor device according to claim 2, wherein  
a native oxide film or a chemical oxide film formed by liquid chemical treatment is formed between  
the first polycrystalline silicon film and the second polycrystalline silicon film.

---